



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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SILICON CONTROLLED RECTIFIER

Qualified per MIL-PRF-19500/ 276

Devices

2N2323	2N2324	2N2326	2N2328	
2N2323S	2N2324S	2N2326S	2N2328S	2N2329
2N2323A	2N2324A	2N2326A	2N2328A	2N2329S
2N2323AS	2N2324AS	2N2326AS	2N2328AS	

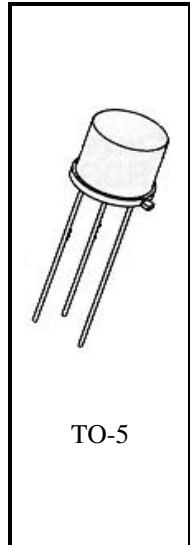
Qualified Level

JAN
JANTX
JANTXV

MAXIMUM RATINGS

Ratings	Sym	2N2323,S/ 2N2323A,S	2N2324,S/ 2N2324A,S	2N2326,S/ 2N2326A,S	2N2328,S/ 2N2328A,S	2N2329,S	Unit	
Reverse Voltage	V _{RM}	50	100	200	300	400	Vdc	
Working Peak Reverse Voltage	V _{RM}	75	150	300	400	500	Vpk	
Forward Blocking Voltage	V _{F BXM}	50 ^(3/4)	100 ^(3/4)	200 ^(3/4)	300 ^(3/4)	400 ⁽³⁾	Vpk	
Average Forward Current ⁽¹⁾	I _O	0.22						Adc
Forward Current Surge Peak ⁽²⁾	I _{FSM}	15						Adc
Cathode-Gate Current	V _{KGM}	6						Vpk
Operating Temperature	T _{OP}	-65 to +125						°C
Storage Junction Temp	T _{STG}	-65 to +150						°C

- 1) This average forward current is for an ambient temperature of 80°C and 180 electrical degrees of conduction.
- 2) Surge current is non-recurrent. The rate of rise of peak surge current shall not exceed 40 A during the first 5 μs after switching from the 'off' (blocking) to the 'on' (conducting) state. This is measured from the point where the thyristor voltage has decayed to 90% of its initial blocking value.
- 3) Gate connected to cathode through 1,000 ohm resistor.
- 4) Gate connected to cathode through 2,000 ohm resistor.



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
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SUBGROUP 2 TESTING

Reverse Blocking Current				
R ₂ = 1 kμ	2N2323 thru 2N2329 2N2323S thru 2N2329S			
R ₂ = 2 kμ	2N2323A thru 2N2328A 2N2323AS thru 2N2328AS			
V _R = 50 Vdc	2N2323, S, A, AS		10	μAdc
V _R = 100 Vdc	2N2324, S, A, AS			
V _R = 200 Vdc	2N2326, S, A, AS			
V _R = 300 Vdc	2N2328, S, A, AS			
V _R = 400 Vdc	2N2329, S,			

2N2323, A, AS, S; 2N2324, A, AS, S; 2N2326, A, AS, S; 2N2328, A, AS, S; 2N232, S JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
Forward Blocking Current $R_2 = 1\text{ k}\Omega$ 2N2323 thru 2N2329 2N2323S thru 2N2329S $R_2 = 2\text{ k}\Omega$ 2N2323A thru 2N2328A 2N2323AS thru 2N2328AS $V_R = 50\text{ Vdc}$ 2N2323, S, A, AS $V_R = 100\text{ Vdc}$ 2N2324, S, A, AS $V_R = 200\text{ Vdc}$ 2N2326, S, A, AS $V_R = 300\text{ Vdc}$ 2N2328, S, A, AS $V_R = 400\text{ Vdc}$ 2N2329, S	I_{FBX1}		10	μAdc
Reverse Gate Current $V_{KG} = 6\text{ Vdc}$	I_{KG}		200	μAdc
Gate Trigger Voltage and Current $V_2 = V_{FBX} = 6\text{ Vdc}$; $R_L = 100\ \Omega$ $R_e = 1\text{ k}\Omega$ 2N2323 thru 2N2329 and 2N2323S thru 2N2329S $R_e = 2\text{ k}\Omega$ 2N2323A thru 2N2328A and 2N2323AS thru 2N2328AS	V_{GT1} I_{GT1} V_{GT1} I_{GT1}	0.35 0.35	0.80 200 0.60 20	Vdc μAdc Vdc μAdc

SUBGROUP 4 TESTING

Exponential Rate of Voltage Rise $T_A = 125^\circ\text{C}$ $50\ \Omega \leq R_L \leq 400\ \Omega$, $C = 0.1$ to $1.0\ \mu\text{F}$, repetition rate = 60 pps, test duration = 15 seconds $dv/dt = 1.8\text{ v}/\mu\text{s}$, $R_3 = 1\text{ k}\Omega$ 2N2323 thru 2N2329 and 2N2323S thru 2N2329S $dv/dt = 0.7\text{ v}/\mu\text{s}$, $R_3 = 2\text{ k}\Omega$ 2N2323A thru 2N2328A and 2N2323AS thru 2N2328AS $V_{AA} = 50\text{ Vdc}$ 2N2323, S, A, AS $V_{AA} = 100\text{ Vdc}$ 2N2324, S, A, AS $V_{AA} = 200\text{ Vdc}$ 2N2326, S, A, AS $V_{AA} = 300\text{ Vdc}$ 2N2328, S, A, AS $V_{AA} = 400\text{ Vdc}$ 2N2329, S	V_{FBX}			Vdc
Forward "on" Voltage $i_{FM} = 4\text{a (pk)}$ (pulse), pulse width = 8.5 ms, max; duty cycle = 2% max	V_{FM}		2.2	V(pk)
Holding Current $V_{AA} = 24\text{ Vdc}$ max, $I_{F1} = 100\text{ mAdc}$, $I_{F2} = 10\text{ mAdc}$ Gate trigger source voltage = 6 Vdc, trigger pulse width = 25 μs min., $R_2 = 330\ \Omega$ $R_3 = 1\text{ k}\Omega$ 2N2323 thru 2N2329 and 2N2323S thru 2N2329S $R_3 = 2\text{ k}\Omega$ 2N2323A thru 2N2328A and 2N2323AS thru 2N2328AS	I_{HOX}		2.0	mAdc